



P-Channel Enhancement-Mode MOSFET Transistors

PRODUCT SUMMARY

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
VP0300B	-30	2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-1.25
VP0300L		2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-0.32
VP0300LS		2.5 @ $V_{GS} = -12$ V	-2 to -4.5	-0.5
VQ2001J		2 @ $V_{GS} = -12$ V	-2 to -4.5	-0.6
VQ2001P		2 @ $V_{GS} = -12$ V	-2 to -4.5	-0.6

FEATURES

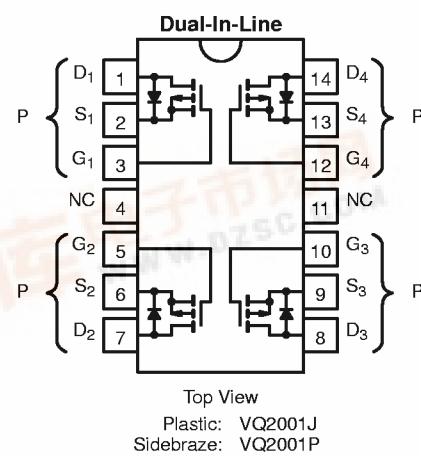
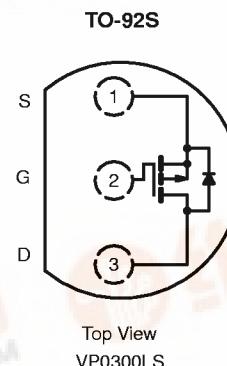
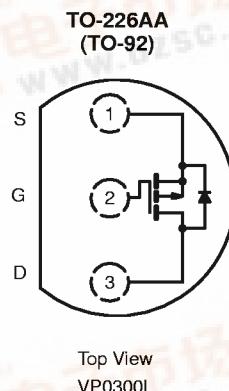
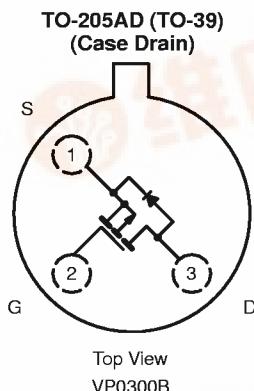
- High-Side Switching
- Low On-Resistance: 1.5 Ω
- Moderate Threshold: -3.1 V
- Fast Switching Speed: 17 ns
- Low Input Capacitance: 60 pF

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Switching
- Easily Driven Without Buffer

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply, Converter Circuits
- Motor Control



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	VP0300B	VP0300L	VP0300LS	VQ2001J/P		Unit
					Single	Total Quad	
Drain-Source Voltage	V_{DS}	-30	-30	-30	-30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	± 20	± 20	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	-1.25 ^b	-0.32	-0.5	-0.6	-0.6	A
		-0.79 ^b	-0.2	-0.32	-0.37	-0.37	
Pulsed Drain Current ^a	I_{DM}	-3	-2.4	-3	-2	-2	W
Power Dissipation	P_D	6.25 ^b	0.8	0.9	1.3	2	
		2.5 ^b	0.32	0.4	0.52	0.8	
Maximum Junction-to-Ambient	R_{thJA}	20 ^b	156	139	96	62.5	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{stg}				-55 to 150		°C

Notes:

a. Pulse width limited by maximum junction temperature.

b. Power dissipation and continuous drain current at $T_C = 25^\circ\text{C}$; $R_{thJC} = 20^\circ\text{C}/\text{W}$.

Applications information may also be obtained via FaxBack, request document #70611.



VP0300B/L/LS, VQ2001J/P

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SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Typ ^a	Limits				Unit	
				VP0300B/L/LS		VQ2001J/P			
				Min	Max	Min	Max		
Static									
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = -10 \mu\text{A}$	-55	-30		-30		V	
Gate-Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -1 \text{ mA}$	-3.1	-2	-4.5	-2	-4.5		
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = \pm 16 \text{ V}$					± 100	nA	
		$T_J = 125^\circ\text{C}$					± 500		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = \pm 20 \text{ V}$			± 100			μA	
		$V_{\text{DS}} = -24 \text{ V}, V_{\text{GS}} = 0 \text{ V}$			-10				
		$T_J = 125^\circ\text{C}$			-500	-500			
On-State Drain Current ^b	$I_{\text{D}(\text{on})}$	$V_{\text{DS}} = -10 \text{ V}, V_{\text{GS}} = -12 \text{ V}$	-2.8	-1.5		-1.5		A	
		$V_{\text{DS}} = -30 \text{ V}, V_{\text{GS}} = 0 \text{ V}$					-10		
Drain-Source On-Resistance ^b	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -12 \text{ V}, I_D = -1 \text{ A}$	1.5		2.5		2	Ω	
		$T_J = 125^\circ\text{C}$	2.6		3.6		3.6		
Forward Transconductance ^b	g_{fs}	$V_{\text{DS}} = -10 \text{ V}, I_D = -0.5 \text{ A}$	370	200		200		mS	
Common Source Output Conductance ^b	g_{os}	$V_{\text{DS}} = -7.5 \text{ V}, I_D = -0.05 \text{ A}$	0.25						
Dynamic									
Input Capacitance	C_{iss}	$V_{\text{DS}} = -15 \text{ V}, V_{\text{GS}} = 0 \text{ V}$ $f = 1 \text{ MHz}$	60		150		150	pF	
Output Capacitance	C_{oss}		40		100		100		
Reverse Transfer Capacitance	C_{rss}		10		60		60		
Switching^c									
Turn-On Time	t_{ON}	$V_{\text{DD}} = -25 \text{ V}, R_L = 23 \Omega$ $I_D \approx -1 \text{ A}, V_{\text{GEN}} = -10 \text{ V}$ $R_G = 25 \Omega$	19		30			ns	
Turn-Off Time	t_{OFF}		17		30				
Turn-On Time	t_{ON}	$V_{\text{DD}} = -15 \text{ V}, R_L = 23 \Omega$ $I_D \approx -0.6 \text{ A}, V_{\text{GEN}} = -10 \text{ V}$ $R_G = 25 \Omega$	19			30			
Turn-Off Time	t_{OFF}		16				30		

Notes

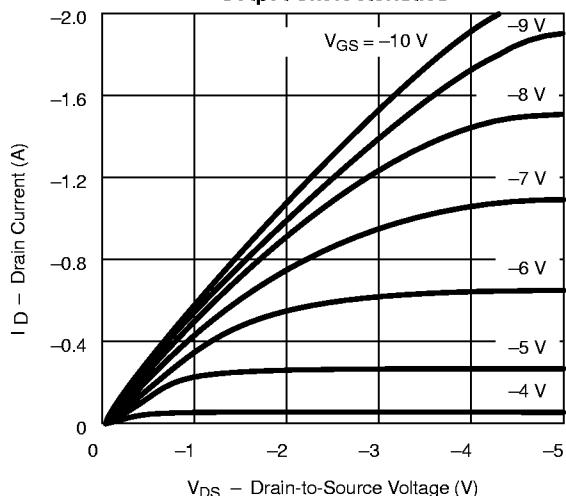
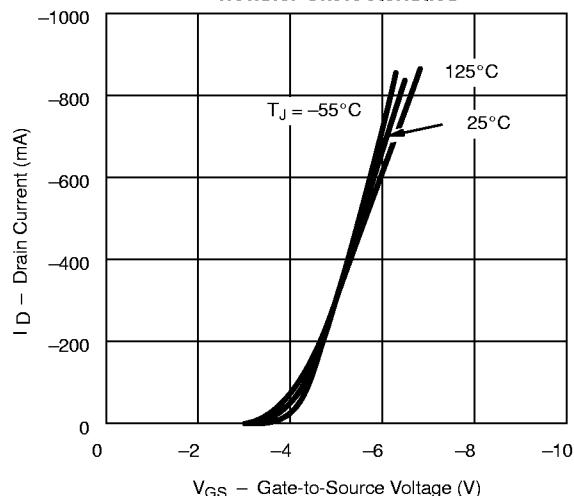
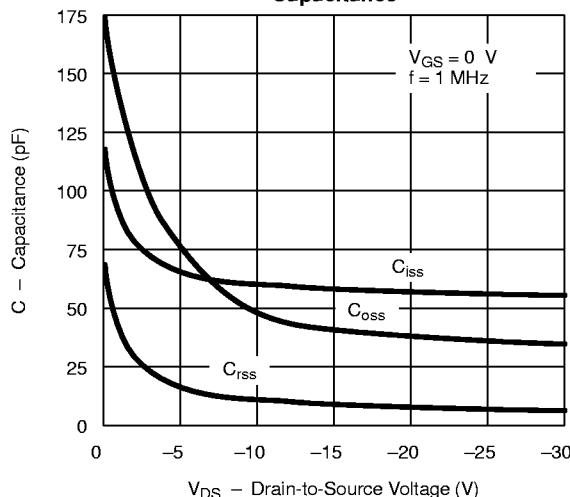
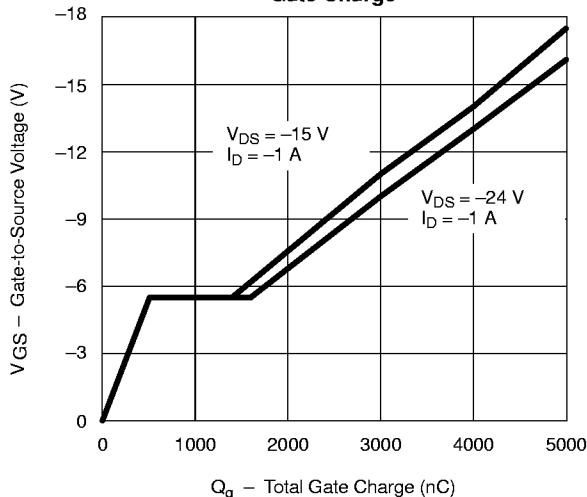
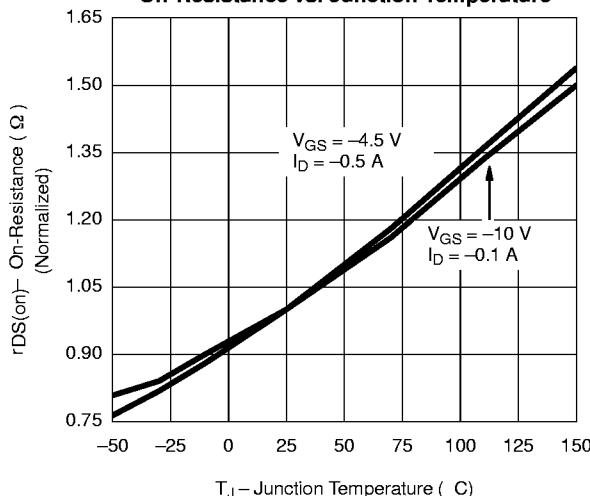
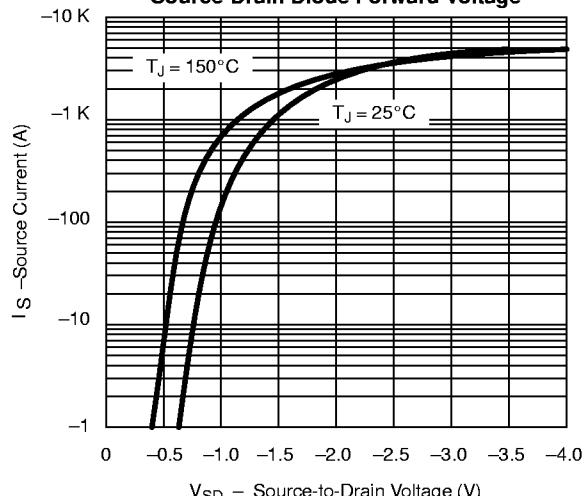
- a. For DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW $\leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.
- c. Switching time is essentially independent of operating temperature.

VPEA03



VP0300B/L/LS, VQ2001J/P

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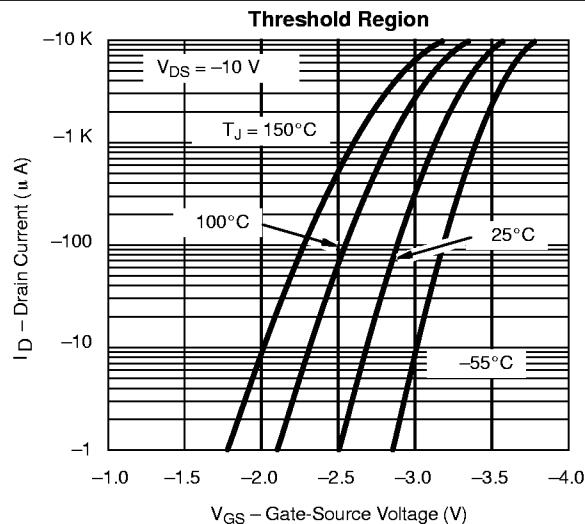
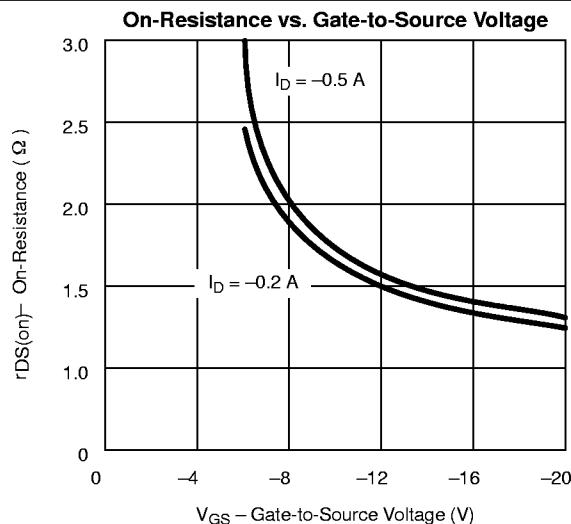
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**Output Characteristics****Transfer Characteristics****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage**

VP0300B/L/LS, VQ2001J/P

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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

